

TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

# TC7MH540FK,TC7MH541FK

## Octal Bus Buffer TC7MH540FK Inverted, 3-State Outputs TC7MH541FK Non-Inverted, 3-State Outputs

The TC7MH540FK and TC7MH541FK are advanced high speed CMOS octal bus buffers fabricated with silicon gate  $\rm C^2MOS$  technology.

They achieve the high speed operation similar to equivalent bipolar schottky TTL while maintaining the CMOS low power dissipation.

The TC7MH540FK is an inverting type, and the TC7MH541FK is a non-inverting type.

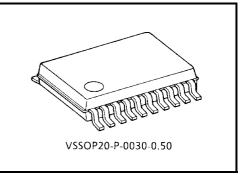
When either  $\overline{G}1$  or  $\overline{G}2$  are high, the terminal outputs are in the high-impedance state.

An input protection circuit ensures that 0 to 7 V can be applied

to the input pins without regard to the supply voltage. This device can be used to interface 5 V to 3 V systems and two supply systems such as battery back up. This circuit prevents device destruction due to mismatched supply and input voltages.

## Features

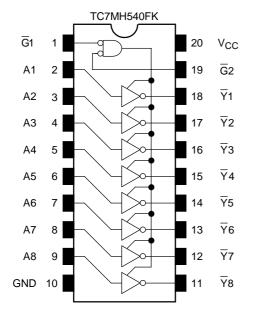
- High speed:  $t_{pd} = 3.7 \text{ ns} (typ.) (V_{CC} = 5 \text{ V})$
- Low power dissipation:  $I_{CC} = 4 \mu A (max) (T_a = 25^{\circ}C)$
- High noise immunity:  $V_{NIH} = V_{NIL} = 28\% V_{CC}$  (min)
- Power down protection is provided on all inputs.
- Balanced propagation delays:  $t_pLH \approx t_pHL$
- Wide operating voltage range:  $V_{CC}$  (opr) = 2~5.5 V
- Low noise: VOLP = 1.0 V (max)
- Pin and function compatible with 74ALS540/541

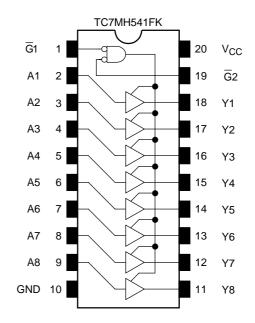


Weight: 0.03 g (typ.)

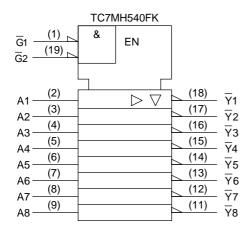
## **TOSHIBA**

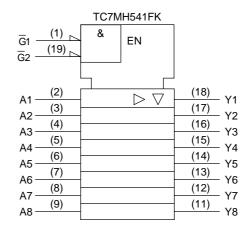
## Pin Assignment (top view)





## **IEC Logic Symbol**





#### **Truth Table**

	Inputs	Outputs				
G1	G2	A <sub>n</sub>	Y <sub>n</sub> (541)	<u> </u>		
Н	Х	Х	Z	Z		
Х	Н	Х	Z	Z		
L	L	Н	Н	L		
L	L	L	L	Н		

X: Don't care

Z: High impedance

Yn: TC7MH541

 $\overline{Y}_n$  : TC7MH540

## **Maximum Ratings**

Characteristics	Symbol	Rating	Unit
Supply voltage range	V <sub>CC</sub>	-0.5~7.0	V
DC input voltage	V <sub>IN</sub>	-0.5~7.0	V
DC output voltage	Vout	$-0.5 \sim V_{CC} + 0.5$	V
Input diode current	I <sub>IK</sub>	-20	mA
Output diode current	I <sub>OK</sub>	±20	mA
DC output current	IOUT	±25	mA
DC V <sub>CC</sub> /ground current	ICC	±75	mA
Power dissipation	PD	180	mW
Storage temperature	T <sub>stg</sub>	-65~150	°C

## **Recommended Operating Conditions**

Characteristics	Symbol	Rating	Unit
Supply voltage	V <sub>CC</sub>	2.0~5.5	V
Input voltage	V <sub>IN</sub>	0~5.5	V
Output voltage	V <sub>OUT</sub>	0~V <sub>CC</sub>	V
Operating temperature	T <sub>opr</sub>	-40~85	°C
Input rise and fall time	dt/dv	0~100 (V_{CC} = 3.3 $\pm$ 0.3 V)	ns/V
	u, uv	0~20 (V <sub>CC</sub> = 5 $\pm$ 0.5 V)	113/ V

## **Electrical Characteristics**

## **DC** Characteristics

Characteristics Symbol Test C		Symbol	Symbol Test Condition			Ta = 25°C			Ta = -40~85°C		Unit
		V <sub>CC</sub> (V		Min	Тур.	Max	Min	Max	Unit		
High level						1.50			1.50	_	
	High level	VIH			3.0~5.5	$\begin{array}{c} V_{CC} \\ \times \ 0.7 \end{array}$	_	_	$V_{CC} \times 0.7$	_	V
Input voltage							_	0.50	_	0.50	v
	Low level	VIL	—		3.0~5.5		_	$V_{CC} \times 0.3$	_	$V_{CC} \times 0.3$	
		Vон		I <sub>OH</sub> = -50 μA	2.0	1.9	2.0	—	1.9	_	
			V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub>		3.0	2.9	3.0		2.9	_	
Output voltage	High level				4.5	4.4	4.5		4.4	—	V
				$I_{OH} = -4 \text{ mA}$	3.0	2.58	_	_	2.48	—	
				$I_{OH} = -8 \text{ mA}$	4.5	3.94	_	_	3.80	—	
Output voltage		V <sub>OL</sub>	V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub>	I <sub>OL</sub> = 50 μA	2.0	_	0	0.1	_	0.1	
					3.0	_	0	0.1	—	0.1	
	Low level				4.5	_	0	0.1		0.1	
				$I_{OL} = 4 \text{ mA}$	3.0	_	—	0.36		0.44	
			$I_{OL} = 8 \text{ mA}$	4.5	_	—	0.36	—	0.44		
3-state output off-state current $I_{OZ}$ $V_{IN} = V_{IH} \text{ or } V_{IL}$ $V_{OUT} = V_{CC} \text{ or } GND$			5.5	_	—	±0.25	_	±2.50	μΑ		
Input leakage cu	irrent	I <sub>IN</sub>	V <sub>IN</sub> = 5.5 V or GND		0~5.5			±0.1		±1.0	μA
Quiescent suppl	ent supply current $I_{CC}$ $V_{IN} = V_{CC}$ or GND		5.5			4.0	_	40.0	μA		

## AC Characteristics (Input: $t_r = t_f = 3 \text{ ns}$ )

Characteristics	Sympol	Test Condition			Ta = 25°C			Ta = -40~85°C		Unit
Characteristics	Symbol	Test Condition	$V_{CC}(V)$	C <sub>L</sub> (pF)	Min	Тур.	Max	Min	Max	Unit
			3.3 ± 0.3 -	15		4.8	7.0	1.0	8.5	ns
Propagation delay time	t <sub>pLH</sub>			50	_	7.3	10.5	1.0	12.0	
(TC7MH540FK)	t <sub>pHL</sub>		5.0 ± 0.5	15		3.7	5.0	1.0	6.0	
			5.0 ± 0.5	50		5.2	7.0	1.0	8.0	
			3.3 ± 0.3	15		5.0	7.0	1.0	8.5	
Propagation delay time	t <sub>pLH</sub>		5.5 ± 0.5	50		7.5	10.5	1.0	12.0	ns
(TC7MH541FK)	t <sub>pHL</sub>	_	$5.0\pm0.5$	15		3.5	5.0	1.0	6.0	ns
				50		5.0	7.0	1.0	8.0	
	t <sub>pZL</sub> t <sub>pZH</sub>	$R_L = 1 \ k\Omega$	$\textbf{3.3}\pm\textbf{0.3}$	15		6.8	10.5	1.0	12.5	ns
3-state output enable time				50		9.3	14.0	1.0	16.0	
			$5.0\pm0.5$	15		4.7	7.2	1.0	8.5	
				50		6.2	9.2	1.0	10.5	
3-state output disable time	t <sub>pLZ</sub>	Rι = 1 kΩ	$\textbf{3.3}\pm\textbf{0.3}$	50		11.2	15.4	1.0	17.5	ns
	t <sub>pHZ</sub>	KL = 1 KS2	$5.0\pm0.5$	50		6.0	8.8	1.0	10.0	115
Output to output skew	t <sub>osLH</sub>	(Note1)	$\textbf{3.3}\pm\textbf{0.3}$	50			1.5		1.5	ns
	t <sub>osHL</sub>	(Noter)	$5.0\pm0.5$	50			1.0		1.0	115
Input capacitance	C <sub>IN</sub>	—			4	10	_	10	pF	
Output capacitance	C <sub>OUT</sub>	_			6	_			pF	
Power dissipation	6	TC7MH540FK TC7MH541FK				17		_	_	рĘ
capacitance (Note2)	C <sub>PD</sub>				18			_	рF	

Note1: Parameter guaranteed by design.

 $t_{OSLH} = |t_{pLHm} - t_{pLHn}|, t_{OSHL} = |t_{pHLm} - t_{pHLn}|$ 

Note2: C<sub>PD</sub> is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

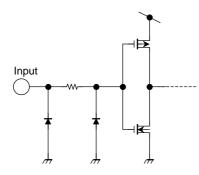
Average operating current can be obtained by the equation:

 $I_{CC (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/8$  (per bit)

## Noise Characteristics (Input: $t_r = t_f = 3 \text{ ns}$ )

Characteristics	Symbol	Test Condition	-	Ta = 25°C		Unit
Characteristics	Symbol		$V_{CC}(V)$	Тур.	Limit	Unit
Quiet output maximum dynamic $V_{OL}$	V <sub>OLP</sub>	C <sub>L</sub> = 50 pF	5.0	0.7	1.0	V
Quiet output minimum dymnamic $V_{OL}$	V <sub>OLV</sub>	C <sub>L</sub> = 50 pF	5.0	-0.7	-1.0	V
Minimum high level dynamic input voltage $\mathrm{V}_{\mathrm{IH}}$	V <sub>IHD</sub>	C <sub>L</sub> = 50 pF	5.0	_	1.5	V
Maximum low level dynamic input voltage $V_{IL}$	V <sub>ILD</sub>	C <sub>L</sub> = 50 pF	5.0	_	3.5	V

## Input Equivalent Circuit

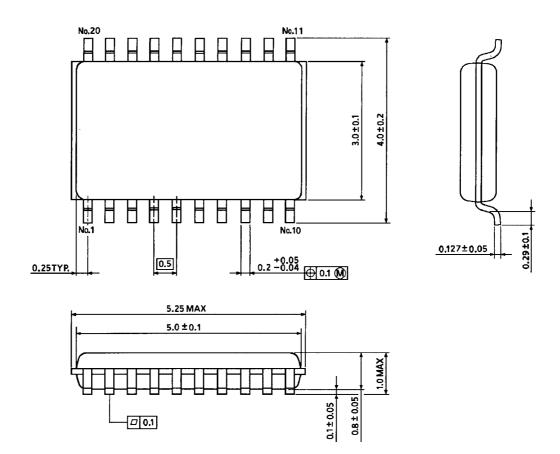




#### **Package Dimensions**

VSSOP20-P-0030-0.50

Unit : mm



Weight: 0.03 g (typ.)

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Handbook" etc..

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